

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA2573FK

Low-Voltage Octal D-Type Latch with 3.6 V Tolerant Inputs and Outputs

The TC7MA2573FK is a high performance CMOS octal D-type latch. Designed for use in 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

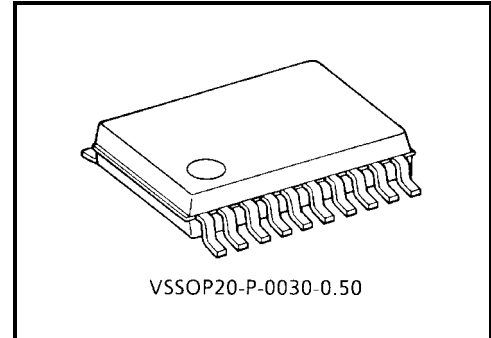
It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

This 8 bit D-type latch is controlled by a latch enable input (LE) and an output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

The 26 Ω series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.



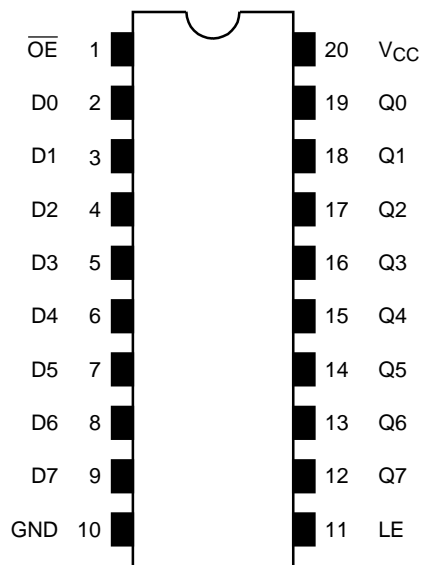
Weight: 0.03 g (typ.)

Features

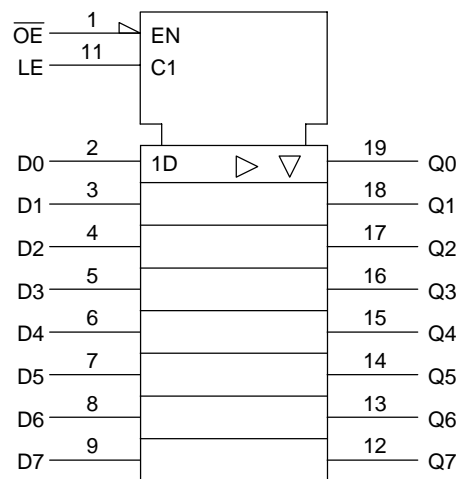
- 26 Ω series resistors on outputs.
- Low voltage operation: $V_{CC} = 1.8\sim 3.6$ V
- High speed operation: $t_{pd} = 5.1$ ns (max) ($V_{CC} = 3.0\sim 3.6$ V)
 $t_{pd} = 6.1$ ns (max) ($V_{CC} = 2.3\sim 2.7$ V)
 $t_{pd} = 9.8$ ns (max) ($V_{CC} = 1.8$ V)
- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 12$ mA (min) ($V_{CC} = 3.0$ V)
 $I_{OH}/I_{OL} = \pm 8$ mA (min) ($V_{CC} = 2.3$ V)
 $I_{OH}/I_{OL} = \pm 4$ mA (min) ($V_{CC} = 1.8$ V)
- Latch-up performance: ± 300 mA
- ESD performance: Machine model $> \pm 200$ V
Human body model $> \pm 2000$ V
- Package: VSSOP (US20)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)

*: To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

Pin Assignment (top view)



IEC Logic Level



Truth Table

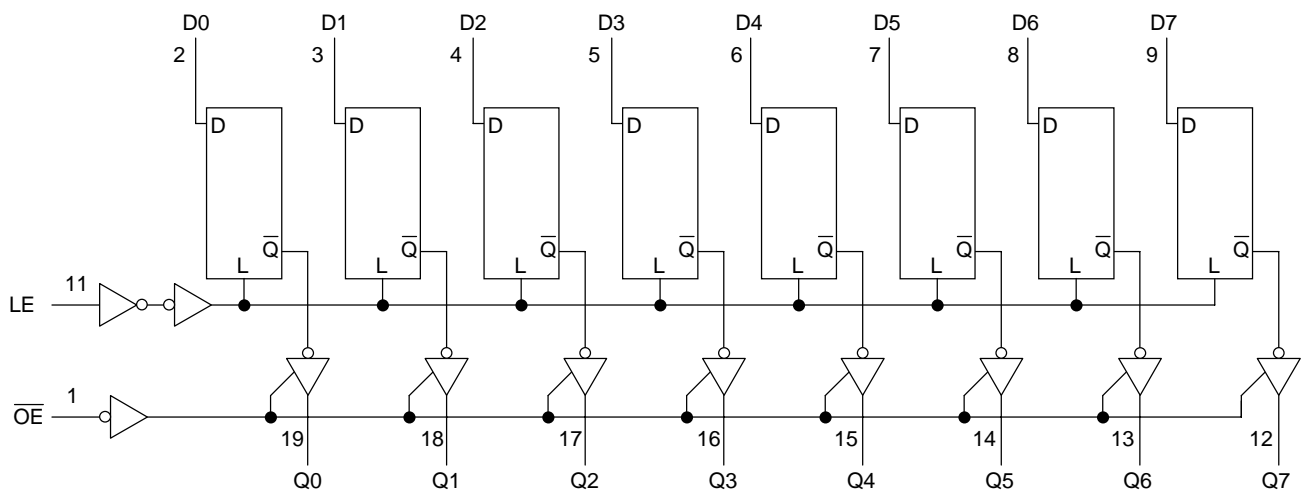
Inputs			Outputs
\overline{OE}	LE	D	
H	X	X	Z
L	L	X	Q_n
L	H	L	L
L	H	H	H

X: Don't care

Z: High impedance

Q_n : Q outputs are latched at the time when the LE inputs is taken to a low logic level.

System Diagram



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	-0.5~4.6	V
DC input voltage	V_{IN}	-0.5~4.6	V
DC output voltage	V_{OUT}	-0.5~4.6 (Note1)	V
		-0.5~ $V_{CC} + 0.5$ (Note2)	
Input diode current	I_{IK}	-50	mA
Output diode current	I_{OK}	± 50 (Note3)	mA
DC output current	I_{OUT}	± 50	mA
Power dissipation	P_D	180	mW
DC V_{CC} /ground current	I_{CC}/I_{GND}	± 100	mA
Storage temperature	T_{stg}	-65~150	°C

Note1: Off-state

Note2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note3: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	1.8~3.6	V
		1.2~3.6 (Note4)	
Input voltage	V_{IN}	-0.3~3.6	V
Output voltage	V_{OUT}	0~3.6 (Note5)	V
		0~ V_{CC} (Note6)	
Output current	I_{OH}/I_{OL}	± 12 (Note7)	mA
		± 8 (Note8)	
		± 4 (Note9)	
Operating temperature	T_{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V

Note4: Data retention only

Note5: Off-state

Note6: High or low state

Note7: $V_{CC} = 3.0\text{~}3.6$ V

Note8: $V_{CC} = 2.3\text{~}2.7$ V

Note9: $V_{CC} = 1.8$ V

Note10: $V_{IN} = 0.8\text{~}2.0$ V, $V_{CC} = 3.0$ V

Electrical Characteristics

DC Characteristics (Ta = -40~85°C, 2.7 V < VCC ≤ 3.6 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	High level	V _{IH}	—		2.7~3.6	2.0	—	V
	Low level	V _{IL}	—		2.7~3.6	—	0.8	
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	2.7	2.2	—	
				I _{OH} = -8 mA	3.0	2.4	—	
				I _{OH} = -12 mA	3.0	2.2	—	
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7~3.6	—	0.2	
				I _{OL} = 6 mA	2.7	—	0.4	
				I _{OL} = 8 mA	3.0	—	0.55	
				I _{OL} = 12 mA	3.0	—	0.8	
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	—	±5.0	μA
3-state output off-state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		2.7~3.6	—	±10.0	μA
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.7~3.6	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7~3.6	—	±20.0	
		ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V (per input)		2.7~3.6	—	750	

DC Characteristics (Ta = -40~85°C, 2.3 V ≤ VCC ≤ 2.7 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	High level	V _{IH}	—		2.3~2.7	1.6	—	V
	Low level	V _{IL}	—		2.3~2.7	—	0.7	
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	—	V
				I _{OH} = -4 mA	2.3	2.0	—	
				I _{OH} = -6 mA	2.3	1.8	—	
				I _{OH} = -8 mA	2.3	1.7	—	
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3~2.7	—	0.2	
				I _{OL} = 6 mA	2.3	—	0.4	
				I _{OL} = 8 mA	2.3	—	0.6	
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	—	±5.0	μA
3-state output off-state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		2.3~2.7	—	±10.0	μA
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.3~2.7	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3~2.7	—	±20.0	

DC Characteristics (Ta = -40~85°C, 1.8 V ≤ VCC < 2.3 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	High level	V _{IH}	—		1.8~2.3	0.7 × V _{CC}	—	V
	Low level	V _{IL}	—		1.8~2.3	—	0.2 × V _{CC}	
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	—	V
				I _{OH} = -4 mA	1.8	1.4	—	
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.8	—	0.2	
				I _{OL} = 4 mA	1.8	—	0.3	
Input leakage current		I _{IN}	V _{IN} = 0~3.6 V		1.8	—	±5.0	μA
3-state output off-state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		1.8	—	±10.0	μA
Power off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		1.8	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		1.8	—	±20.0	

AC Characteristics (Ta = -40~85°C, Input: tr = tf = 2.0 ns, CL = 30 pF, RL = 500 Ω)

Characteristics	Symbol	Test Condition	VCC (V)	Min	Max	Unit
			1.8	1.5	9.8	
Propagation delay time (D-Q)	t _{pLH} t _{pHL}	Figure 1, Figure 2	2.5 ± 0.2	0.8	6.1	ns
			3.3 ± 0.3	0.6	5.1	
			1.8	1.5	9.8	
Propagation delay time (LE-Q)	t _{pLH} t _{pHL}	Figure 1, Figure 2	2.5 ± 0.2	0.8	6.3	ns
			3.3 ± 0.3	0.6	5.1	
			1.8	1.5	9.8	
3-state output enable time	t _{pZL} t _{pZH}	Figure 1, Figure 3	2.5 ± 0.2	0.8	6.5	ns
			3.3 ± 0.3	0.6	5.0	
			1.8	1.5	7.7	
3-state output disable time	t _{pLZ} t _{pHZ}	Figure 1, Figure 3	2.5 ± 0.2	0.8	4.3	ns
			3.3 ± 0.3	0.6	3.9	
			1.8	1.5	9.8	
Minimum pulse width (LE)	t _{w (H)}	Figure 1, Figure 2	2.5 ± 0.2	1.5	—	ns
			3.3 ± 0.3	1.5	—	
			1.8	4.0	—	
Minimum set-up time	t _s	Figure 1, Figure 2	2.5 ± 0.2	1.5	—	ns
			3.3 ± 0.3	1.5	—	
			1.8	2.5	—	
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0	—	ns
			3.3 ± 0.3	1.0	—	
			1.8	1.0	—	
Output to output skew	t _{osLH} t _{osHL}	(Note11)	2.5 ± 0.2	—	1.5	ns
			3.3 ± 0.3	—	1.5	
			1.8	—	1.5	

For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics (Ta = 25°C, Input: tr = tf = 2.0 ns, CL = 30 pF)

Characteristics	Symbol	Test Condition	VCC (V)	Typ.	Unit
Quiet output maximum dynamic VOL	VOLP	VIH = 1.8 V, VIL = 0 V (Note12)	1.8	0.15	V
		VIH = 2.5 V, VIL = 0 V (Note12)	2.5	0.25	
		VIH = 3.3 V, VIL = 0 V (Note12)	3.3	0.35	
Quiet output minimum dynamic VOL	VOLV	VIH = 1.8 V, VIL = 0 V (Note12)	1.8	-0.15	V
		VIH = 2.5 V, VIL = 0 V (Note12)	2.5	-0.25	
		VIH = 3.3 V, VIL = 0 V (Note12)	3.3	-0.35	
Quiet output minimum dynamic VOH	VOHV	VIH = 1.8 V, VIL = 0 V (Note12)	1.8	1.55	V
		VIH = 2.5 V, VIL = 0 V (Note12)	2.5	2.05	
		VIH = 3.3 V, VIL = 0 V (Note12)	3.3	2.65	

Note12: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

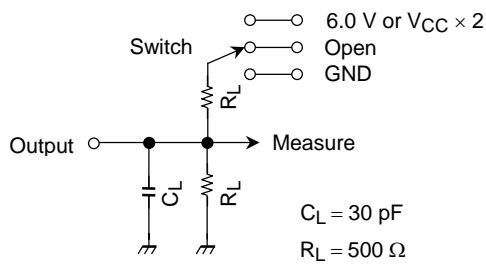
Characteristics	Symbol	Test Condition	VCC (V)	Typ.	Unit
Input capacitance	CIN	—	1.8, 2.5, 3.3	6	pF
Output capacitance	COU	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	CPD	fIN = 10 MHz (Note13)	1.8, 2.5, 3.3	20	pF

Note13: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$$

AC Test Circuit



Parameter	Switch
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0 V @ $V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} \times 2$ @ $V_{CC} = 2.5 \pm 0.2 \text{ V}$ @ $V_{CC} = 1.8 \text{ V}$
t_{pHZ}, t_{pZH}	GND

Figure 1

AC Waveform

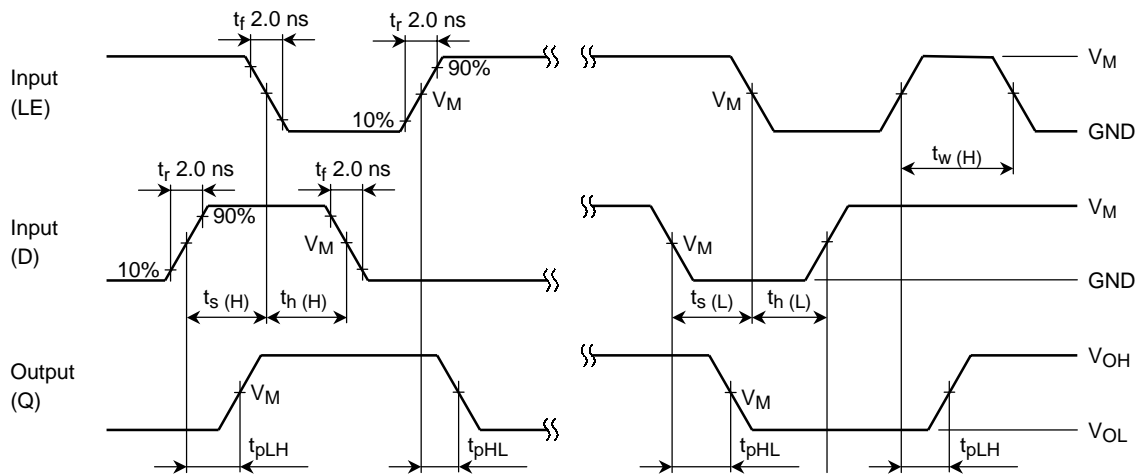


Figure 2 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$

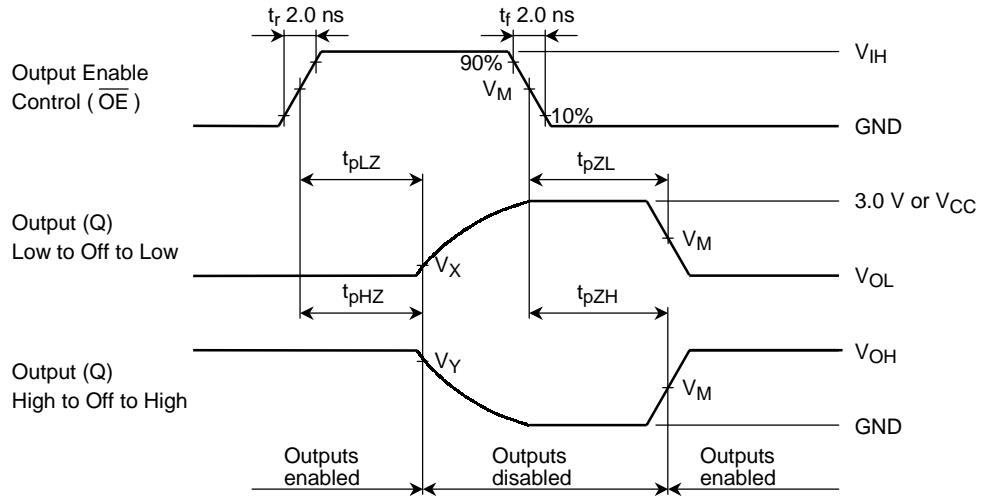


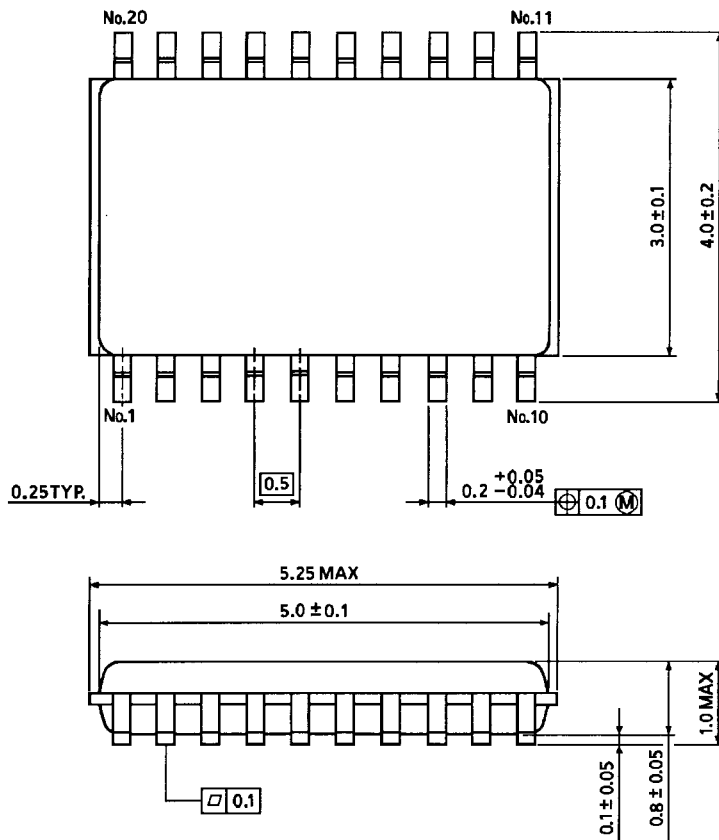
Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol	V_{CC}		
	$3.3 \pm 0.3 \text{ V}$	$2.5 \pm 0.2 \text{ V}$	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3 \text{ V}$	$V_{OL} + 0.15 \text{ V}$	$V_{OL} + 0.15 \text{ V}$
V_Y	$V_{OH} - 0.3 \text{ V}$	$V_{OH} - 0.15 \text{ V}$	$V_{OH} - 0.15 \text{ V}$

Package Dimensions

VSSOP20-P-0030-0.50

Unit : mm



Weight: 0.03 g (typ.)

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000707EBA

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